



Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.356US1	Serial No. 08/902,133
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: July 29, 1997	Group: 2815

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>Wm</i>	4,460,670	07/01/1984	Ogawa, et al.	430	51.7 577	
<i>Wm</i>	4,657,699	04/01/1987	Nair	252	513	
<i>Wm</i>	4,738,729	04/01/1998	Yoshida, et al.	136	258	
<i>Wm</i>	5,145,741	09/01/1992	Quick	428	402	
<i>Wm</i>	5,604,357	02/18/1997	Hori, T.	257	24	07/11/95
<i>Wm</i>	5,801,401	09/01/1998	Forbes, L.	257	77	

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Examiner <i>v. Martin Wallace</i>	Date Considered <i>3/3/99</i>
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<i>Renew</i>	5,714,766	02/03/1998	Chen, et al.	257	20	09/29/95
<i>Renew</i>	5,754,477	05/19/1998	Forbes	365	185.33	01/29/97

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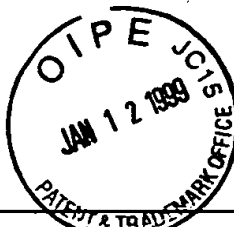
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<u>VMW</u>	5,298,796	03/29/1994	Tawel, R.	307 ⁷⁰⁶	201 ³³	07/08/92
<u>VMW</u>	5,623,442	04/22/1997	Gotou, H., et al.	365	185.08	06/08/94
<u>VMW</u>	5,786,250	07/28/1998	Wu, Z., et al.	438	254	03/14/97

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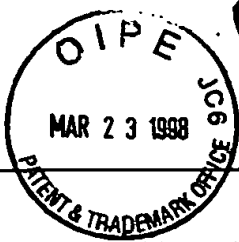
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<i>Vmur</i>	4,893,273	01/09/1990	Usami	365	185 185.04	03/21/86
<i>Vmur</i>	5,111,430	05/05/1992	Morie	365	185 185.24	06/21/90
<i>Vmur</i>	5,260,593	11/09/1993	Lee	257	316	12/10/91
<i>Vmur</i>	5,293,560	03/08/1994	Harari	365	185 185.03	11/03/92
<i>Vmur</i>	5,369,040	11/29/1994	Halvis, et al.	437 438	3 22	04/12/93
<i>Vmur</i>	5,449,941	09/12/1995	Yamazaki, et al.	257	411	10/27/92
<i>Vmur</i>	5,465,249	11/07/1995	Cooper, et al.	365	149	11/26/91
<i>Vmur</i>	5,477,485	12/19/1995	Bergemont, et al.	365	185.24	02/22/95
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<i>Vmur</i>	5,530,581	06/25/1996	Cogan	359	265	05/31/95
<i>Vmur</i>	5,580,380	12/03/1996	Liu, et al.	117	86	01/30/95
<i>Vmur</i>	5,670,790	09/23/1997	Katon, et al.	257	14	09/19/96

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<i>Vmur</i>	6-224431	08/12/1994	Japan	H01L	29/784	
<i>Vmur</i>	6-302828	10/28/1994	Japan	H01L	29/788	
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Vmur	Bengtsson, S., et al., "Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-On-Insulator Materials", <u>Japanese J. Applied Physics</u> , 35, 4175-4181, (1996)
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Vmur	Chang, C., et al., "Novel Passivation Dielectrics-The Boron- or Phosphorus-Doped Hydrogenated Amorphous Silicon Carbide Films", <u>Journal of the Electrochemical Society</u> , 132, 418-422, (Feb. 1985)
Vmur	Choi, J., et al., "Effect of Deposition Conditions and Pretreatments on the Microstructure of MPECVD Diamond Thin Films", <u>Materials Chemistry and Physics</u> , 45, 176-179, (1996)
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Vmur	Compagnini, G., et al., "Spectroscopic Characterization of Annealed Si(1-x)C(x) Films", <u>J. Materials Res.</u> , 11, 2269-2273, (Sept. 1996)
Vmur	Dartnell, N., et al., "Reactive Ion Etching of Silicon Carbide (Si(x)C(1-x))", <u>Vacuum</u> , 46, 349-355, (1995)
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Vmur	Dipert, B., et al., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, 48-52, (1993)

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vmur	Friedrichs, P., et al., "Interface Properties of Metal-Oxide-Semiconductor Structures on N-Type 6H and 4H-SiC", <u>J. Applied Physics</u> , 79, 7814-7819, (May 15, 1996)
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vmur	Goetzberger, A., et al., <u>Applied Solid State Science: Advances in Materials and Device Research</u> , R. Wolfe, ed., Academic Press, New York, Including pg. 233, (1969)
vmur	Graul, J., et al., "Growth Mechanism of Polycrystalline beta-SiC Layers on Silicon Substrate", <u>Applied Phys. Lett.</u> , 21, 67-69, (July 1972)
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vmur	He, Z., et al., "Ion-beam-assisted Deposition of Si-carbide Films", <u>Thin Solid Films</u> , 260, 32-37, (1995)
vmur	Hu, G., "Will Flash Memory Replace Hard Disk Drive?", <u>IEEE Electron Devices Meeting, Session 24</u> , (Dec. 13, 1994)
vmur	Hwang, J., et al., "High Mobility beta-SiC Epilayer Prepared by Low-pressure Rapid Thermal Chemical Vapor Deposition on a (100) Silicon Substrate", <u>Thin Solid Films</u> , 272, 4-6, (1996)
vmur	Jou, S., et al., "Electron Emission Characterization of Diamond Thin Films Grown from a Solid Carbon Source", <u>Thin Solid Films</u> , 280, 256-261, (1996)
vmur	Kothandaraman, M., et al., "Reactive Ion Etching of Trenches in 6H-SiC", <u>J. Electronic Materials</u> , 25, 875-878, (1996)
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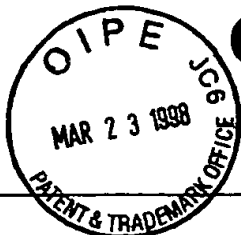
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<i>vmw</i>	Prendergast, J., "FLASH or DRAM: Memory Choice for the Future", <u>IEEE Electron Device Meeting, Session 25</u> , Phoenix, AZ, (1995)
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Examiner

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Date Considered

3/3/99

*Substitute Disclosure Statement Form (PTO-1449)

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